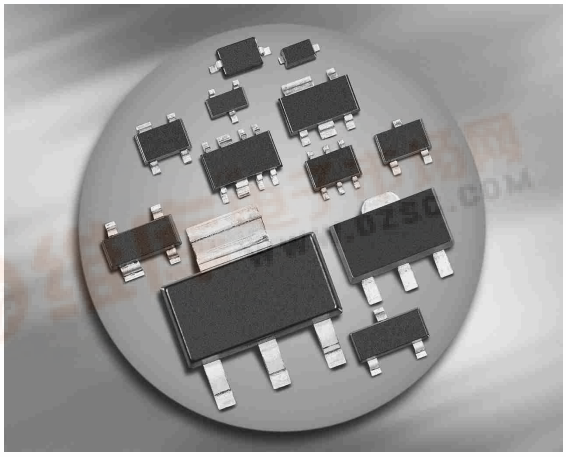
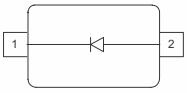
Silicon Variable Capcitance Diode

- For UHF-TV-tuners
- High capacitance ratio
- Low series inductance
- Low series resistance
- Excellent uniformity and matching due to "in-line" matching assembly procedure



BB545
BB565/-02V



Type	Package	Configuration	L_S (nH)	Marking
BB545	SOD323	single	1.8	white U
BB565	SCD80	single	0.6	CC
BB 565-02V	SC79	single	0.6	C

Maximum Ratings at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Peak reverse voltage $R \geq 5k\Omega$	V_{RM}	35	
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 150	°C
Storage temperature	T_{stg}	-55 ... 150	

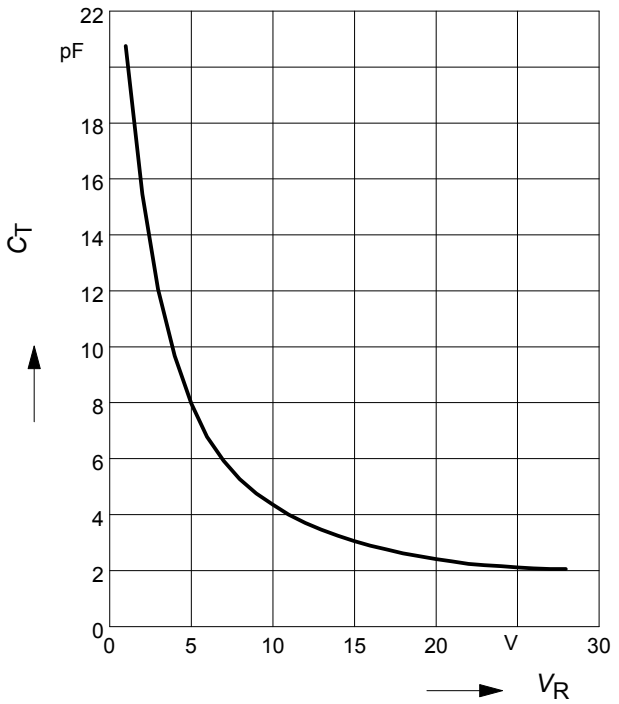
Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current	I_R				nA
V_R = 30 V		-	-	10	
V_R = 30 V, T_A = 85 °C		-	-	200	
AC Characteristics					
Diode capacitance	C_T				pF
V_R = 1 V, f = 1 MHz		18.5	20	21.5	
V_R = 2 V, f = 1 MHz		13.2	14.8	16.4	
V_R = 25 V, f = 1 MHz		1.85	2.07	2.28	
V_R = 28 V, f = 1 MHz		1.8	2	2.2	
Capacitance ratio V_R = 1 V, V_R = 28 V, f = 1 MHz	C_{T1}/C_{T28}	9	10	11	-
Capacitance ratio V_R = 2 V, V_R = 25 V, f = 1 MHz	C_{T2}/C_{T25}	6.3	7.2	8.1	
Capacitance matching[1)] V_R = 1V to 28V, f = 1 MHz, **7** diodes sequence, BB545	$\Delta C_T/C_T$	-	-	2.5	%
V_R = 1V to 28V, f = 1 MHz, **4** diodes sequence, BB565/ -02V		-	0.5	1.5	
V_R = 1V to 28V, f = 1 MHz, **7** diodes sequence, BB565/ -02V		-	0.7	2	
Series resistance V_R = 3 V, f = 470 MHz	r_S	-	0.6	-	Ω

[1]For details please refer to Application Note 047

Diode capacitance $C_T = f(V_R)$

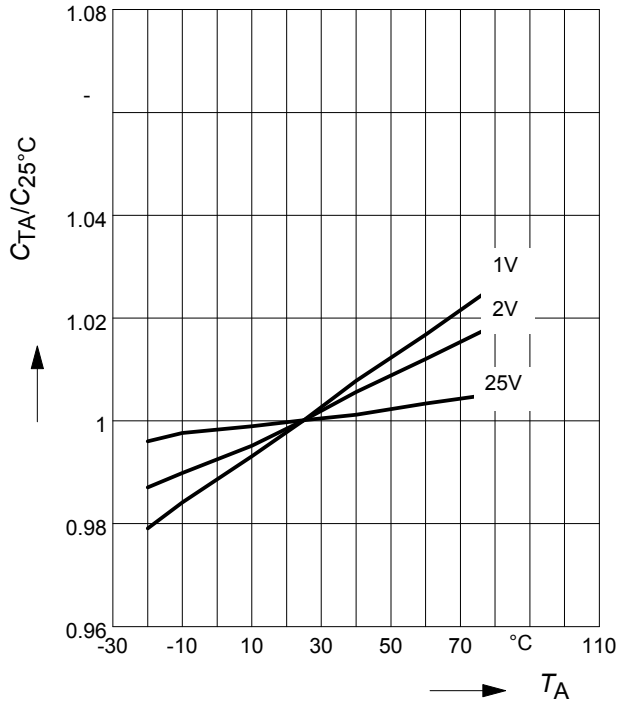
f = 1MHz



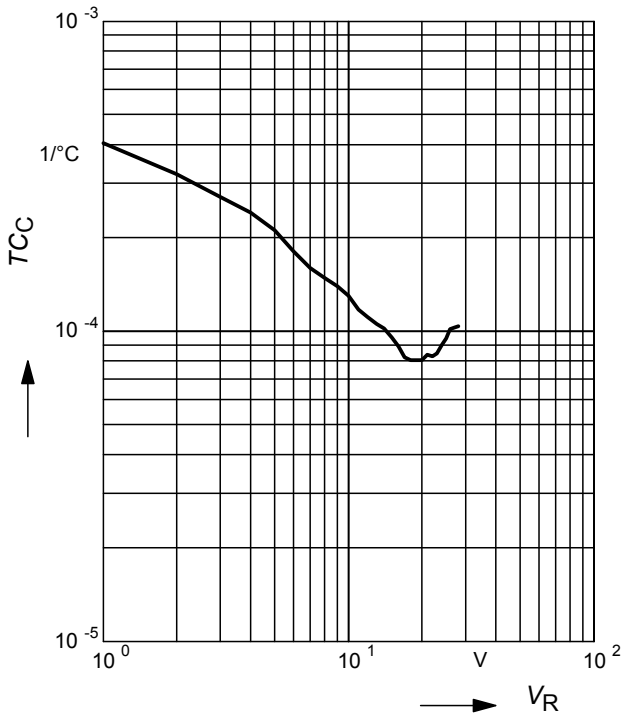
Normalized diode capacitance

$C_{(TA)}/C_{(25°C)} = f(T_A)$; f = 1MHz

V_R = Parameter

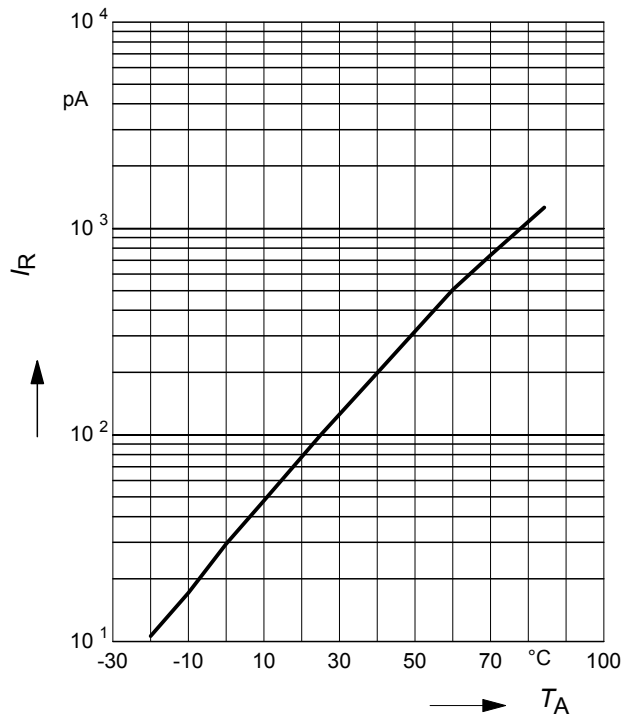


Temperature coefficient of the diode capacitance $T_{Cc} = f(V_R)$



Reverse current $I_R = f(T_A)$

V_R = 28V



Reverse current $I_R = f(V_R)$

T_A = Parameter